PROCESS CP211

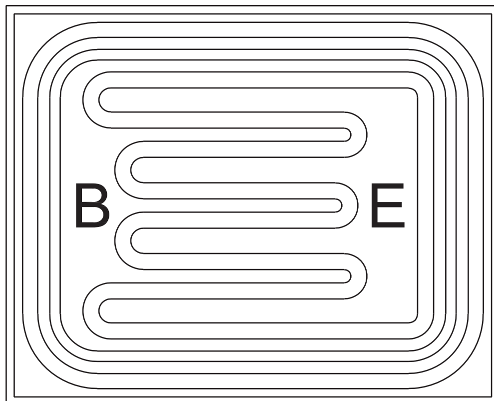
Power Transistor

NPN - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	80 x 99 MILS
Die Thickness	12.5 MILS
Base Bonding Pad Area	12 x 32 MILS
Emitter Bonding Pad Area	13 x 48 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Cr/Ni/Ag - 16,000Å

GEOMETRY



BACKSIDE COLLECTOR R1

GROSS DIE PER 4 INCH WAFER
1,450

PRINCIPAL DEVICE TYPES
2N3054A
CJD41C
TIP41C

R5 (22-March 2010)

PROCESS CP211

Typical Electrical Characteristics